

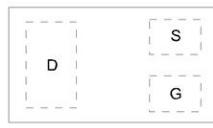
### Product Summary

- $V_{DS}$  60V
- $I_D$  350mA
- $R_{DS(ON)}$  (at  $V_{GS}=10V$ ) <5 ohm
- $R_{DS(ON)}$  (at  $V_{GS}=4.5V$ ) <4.5 ohm
- ESD Protected:2000V

### Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

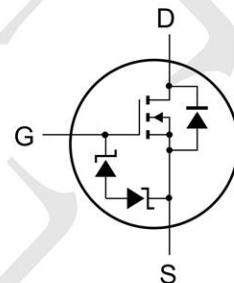
### Package and Pin Configuration



DFN1006-3L

marking:4S

Circuit diagram



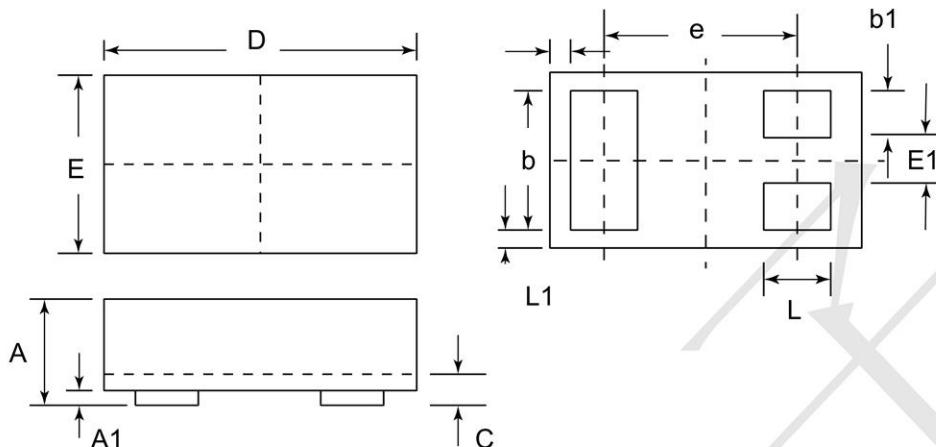
### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$\pm 350$	mA
Power Dissipation	$P_D$	150	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~ +150	°C

**Electrical Characteristics (  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

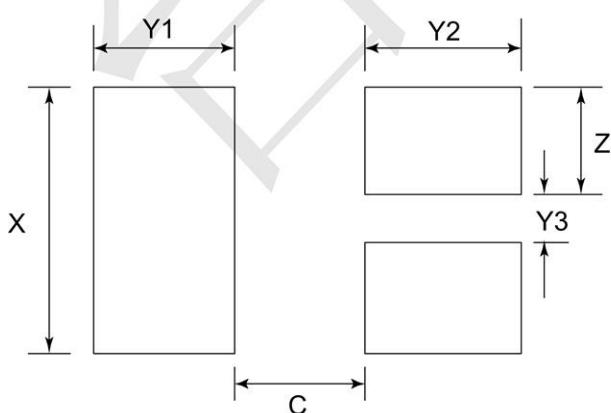
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Drain -Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 10\mu\text{A}$	60			V
		$V_{\text{GS}} = 0\text{V}, I_D = 3\text{mA}$	60			
Gate Threshold Voltage	$V_{\text{th(GS)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.0	1.85	2.5	V
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			$\pm 10$	$\mu\text{A}$
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = 60\text{V}, V_{\text{GS}} = 0\text{V}$			1	$\mu\text{A}$
Static Drain- Source On State Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10\text{V}, I_D = 500\text{mA}$			5	$\Omega$
		$V_{\text{GS}} = 4.5\text{V} I_D = 200\text{mA}$		1.5	4.3	
Input Capacitance	$C_{\text{rss}}$	$V_{\text{GS}} = 10\text{V}$			42	pF
Input Capacitance	$C_{\text{rss}}$	$V_{\text{GS}} = 0\text{V}$			30	
Input Capacitance	$C_{\text{rss}}$	$V_{\text{GS}} = 1\text{MHz}$			10	
Turn-on delay time	$t_{\text{d(on)}}$	$V_{\text{DD}} = 25\text{V}, V_{\text{GS}} = 10\text{V}, R_L = 250\Omega, R_{\text{GS}} = 50\text{K}, R_{\text{GEN}} = 25\Omega$			10	ns
Turn-on delay time	$t_{\text{d(on)}}$				15	

**DFN1006 3L Package Outline Drawing**



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
C	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

**Suggested Land Pattern**



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008

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